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Vladimir Pav	lovich POPOV et al.			
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	OT	HER ART (Includi	ng Author, Title, Date	, Pertinent Dates, Etc.)					
/QJ/	AG	Rieutord, F. et al. "Dynamics of a Bonding Front" Physical Review Letters (2005) PRL Vol. 94							
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/QJ/	AM	Esser, R. H. et al. "Improved Low-Temperature Si-Si Hydrophilic Wafer Bonding"  Journal of the Electrochemical Society (2003) Vol. 150, No. 3, G228-G231							
/QJ/	AN	Dragoi, V. et al. "Plasma Activated Wafer Bonding for MEMS"  SPIE Proceeding 5836 (2005) paper no. 5836-19							
/QJ/	AO	"Long-Term Stability of Vacuum-Encapsulated MEMS Devices Using Eutectic Wafer Bonding"  VABOND-Deliverable 6.4 - Technology Guidelines on Vacuum Encapsulation of MEMS							
/QJ/	AP	Zhang, X. et al. "Low-Temperature Wafer Bonding Optimal O <sub>2</sub> Plasma Surface Pretreatment Time" <i>Electrochemical and Solid-State Letters</i> (2004) Vol. 7, No. 8, G172-G174							
EXAMINER	/Quovauno	da Jefferson/ DATE CONSIDERED 06/19/2007							
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